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(54) Title: NON-VOLATILE ANALOG RESISTIVE MEMORY CELLS IMPLEMENTING FERROELECTRIC SELECT TRANSISTORS

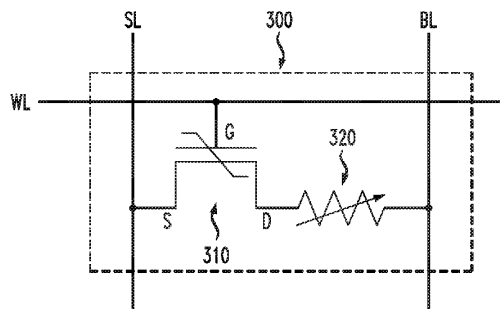


FIG. 3

(57) Abstract: A device includes a non-volatile analog resistive memory cell. The non-volatile analog resistive memory device includes a resistive memory device and a select transistor. The resistive memory device includes a first terminal and a second terminal. The resistive memory device has a tunable conductance. The select transistor is a ferroelectric field-effect transistor (FeFET) device which includes a gate terminal, a source terminal, and a drain terminal. The gate terminal of the FeFET device is connected to a word line. The source terminal of the FeFET device is connected to a source line. The drain terminal of the FeFET device is connected to the first terminal of the resistive memory device. The second terminal of the resistive memory device is connected to a bit line.



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